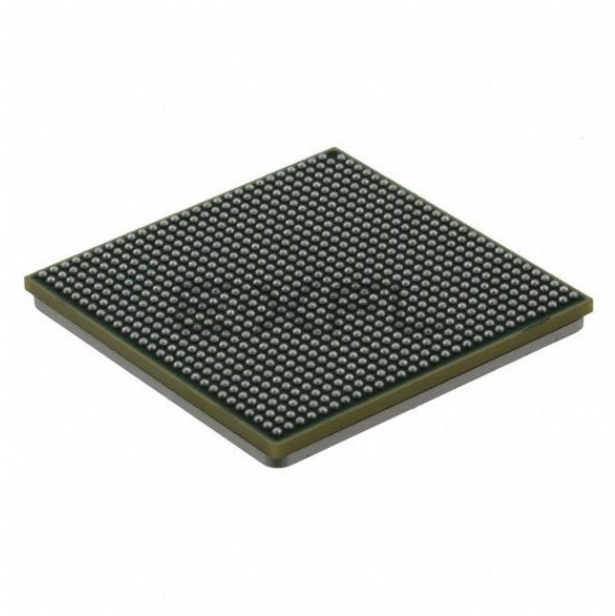

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	833MHz
Co-Processors/DSP	Communications; CPM, Security; SEC
RAM Controllers	DDR, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8555evtapf

- Two full-duplex fast communications controllers (FCCs) that support the following protocols:
  - ATM protocol through two UTOPIA level 2 interfaces
  - IEEE Std 802.3™/Fast Ethernet (10/100)
  - HDLC
  - Totally transparent operation
- Three full-duplex serial communications controllers (SCCs) support the following protocols:
  - High level/synchronous data link control (HDLC/SDLC)
  - LocalTalk (HDLC-based local area network protocol)
  - Universal asynchronous receiver transmitter (UART)
  - Synchronous UART (1x clock mode)
  - Binary synchronous communication (BISYNC)
  - Totally transparent operation
  - QMC support, providing 64 channels per SCC using only one physical TDM interface
- Universal serial bus (USB) controller that is full/low-speed compliant (multiplexed on an SCC)
  - USB host mode
  - Supports USB slave mode
- Serial peripheral interface (SPI) support for master or slave
- I^2C bus controller
- Two serial management controllers (SMCs) supporting:
  - UART
  - Transparent
  - General-circuit interfaces (GCI)
- Time-slot assigner supports multiplexing of data from any of the SCCs and FCCs onto eight time-division multiplexed (TDM) interfaces. The time-slot assigner supports the following TDM formats:
  - T1/CEPT lines
  - T3/E3
  - Pulse code modulation (PCM) highway interface
  - ISDN primary rate
  - Freescale interchip digital link (IDL)
  - General circuit interface (GCI)
- User-defined interfaces
- Eight independent baud rate generators (BRGs)
- Four general-purpose 16-bit timers or two 32-bit timers
- General-purpose parallel ports—16 parallel I/O lines with interrupt capability

• 256 Kbytes of on-chip memory
- Can act as a 256-Kbyte level-2 cache
- Can act as a 256-Kbyte or two 128-Kbyte memory-mapped SRAM arrays

  - PCI 3.3-V compatible
  - Selectable hardware-enforced coherency
  - Selectable clock source (SYSCLK or independent PCI_CLK)
- Power management
  - Fully static 1.2-V CMOS design with 3.3- and 2.5-V I/O
  - Supports power save modes: doze, nap, and sleep
  - Employs dynamic power management
  - Selectable clock source (sysclk or independent PCI_CLK)
- System performance monitor
  - Supports eight 32-bit counters that count the occurrence of selected events
  - Ability to count up to 512 counter specific events
  - Supports 64 reference events that can be counted on any of the 8 counters
  - Supports duration and quantity threshold counting
  - Burstiness feature that permits counting of burst events with a programmable time between bursts
  - Triggering and chaining capability
  - Ability to generate an interrupt on overflow
- System access port
  - Uses JTAG interface and a TAP controller to access entire system memory map
  - Supports 32-bit accesses to configuration registers
  - Supports cache-line burst accesses to main memory
  - Supports large block (4-Kbyte) uploads and downloads
  - Supports continuous bit streaming of entire block for fast upload and download
- IEEE Std 1149.1™-compatible, JTAG boundary scan
- 783 FC-PBGA package

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8555E. The MPC8555E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

Figure 3 shows the undershoot and overshoot voltage of the PCI interface of the MPC8555E for the 3.3-V signals, respectively.

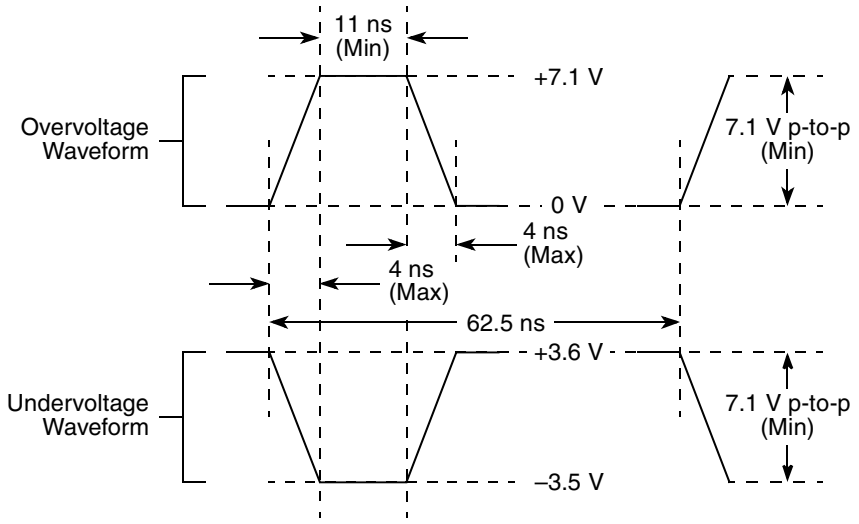

Figure 3. Maximum AC Waveforms on PCI interface for 3.3-V Signaling

2.1.4 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25	OV_{DD} = 3.3 V	1
	42 (default)		
PCI signals	25		2
	42 (default)		
DDR signal	20	GV_{DD} = 2.5 V	
TSEC/10/100 signals	42	LV_{DD} = 2.5/3.3 V	
DUART, system control, I2C, JTAG	42	OV_{DD} = 3.3 V	

Notes:
1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.
2. The drive strength of the PCI interface is determined by the setting of the $\overline{\text{PCI\_GNT1}}$ signal at reset.

3 Power Characteristics

The estimated typical power dissipation for this family of PowerQUICC III devices is shown in Table 4.

Table 4. Power Dissipation(1) (2)

CCB Frequency (MHz)	Core Frequency (MHz)	V_{DD}	Typical Power(3)(4) (W)	Maximum Power(5) (W)
200	400	1.2	4.9	6.6
	500	1.2	5.2	7.0
	600	1.2	5.5	7.3
267	533	1.2	5.4	7.2
	667	1.2	5.9	7.7
	800	1.2	6.3	9.1
333	667	1.2	6.0	7.9
	833	1.2	6.5	9.3
	1000(6)	1.3	9.6	12.8

Notes:

1. The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}.
2. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance. Any customer design must take these considerations into account to ensure the maximum 105 degrees junction temperature is not exceeded on this device.
3. Typical power is based on a nominal voltage of V_{DD} = 1.2V, a nominal process, a junction temperature of T_j = 105° C, and a Dhrystone 2.1 benchmark application.
4. Thermal solutions likely need to design to a value higher than Typical Power based on the end application, T_A target, and I/O power
5. Maximum power is based on a nominal voltage of V_{DD} = 1.2V, worst case process, a junction temperature of T_j = 105° C, and an artificial smoke test.
6. The nominal recommended V_{DD} = 1.3V for this speed grade.

Notes:

1.

2.

3.

4.

5.

6.

4 Clock Timing

4.1 System Clock Timing

Table 6 provides the system clock (SYSCLK) AC timing specifications for the MPC8555E.

Table 6. SYSCLK AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
SYSCLK frequency	f_{SYSCLK}	—	—	166	MHz	1
SYSCLK cycle time	t_{SYSCLK}	6.0	—	—	ns	—
SYSCLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	1.2	ns	2
SYSCLK duty cycle	t_{KHK}/t_{SYSCLK}	40	—	60	%	3
SYSCLK jitter	—	—	—	+/- 150	ps	4, 5

Notes:
1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies.
2. Rise and fall times for SYSCLK are measured at 0.6 and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. For spread spectrum clocking, guidelines are ±1% of the input frequency with a maximum of 60 kHz of modulation regardless of the input frequency.

4.2 TSEC Gigabit Reference Clock Timing

Table 7 provides the TSEC gigabit reference clock (EC_GTX_CLK125) AC timing specifications for the MPC8555E.

Table 7. EC_GTX_CLK125 AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
EC_GTX_CLK125 frequency	f_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—
EC_GTX_CLK125 rise time	t_{G125R}	—	—	1.0	ns	1
EC_GTX_CLK125 fall time	t_{G125F}	—	—	1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI RGMII, RTBI	t_{G125H}/t_{G125}	 45 47	—	 55 53	%	1, 2

Notes:
1. Timing is guaranteed by design and characterization.
2. EC_GTX_CLK125 is used to generate GTX clock for TSEC transmitter with 2% degradation. EC_GTX_CLK125 duty cycle can be loosened from 47/53% as long as PHY device can tolerate the duty cycle generated by GTX_CLK of TSEC.

6 DDR SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the MPC8555E.

6.1 DDR SDRAM DC Electrical Characteristics

Table 11 provides the recommended operating conditions for the DDR SDRAM component(s) of the MPC8555E.

Table 11. DDR SDRAM DC Electrical Characteristics

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.18$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.18$	V	—
Output leakage current	I_{OZ}	–10	10	µA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–15.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	15.2	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	5	µA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 V \le V_{OUT} \le GV_{DD}$.

Table 12 provides the DDR capacitance.

Table 12. DDR SDRAM Capacitance

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, MSYNC_IN	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak to peak) = 0.2 V.

7.2 DUART AC Electrical Specifications

Table 17 provides the AC timing parameters for the DUART interface of the MPC8555E.

Table 17. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	f_{CCB_CLK} / 1048576	baud	3
Maximum baud rate	f_{CCB_CLK} / 16	baud	1, 3
Oversample rate	16	—	2, 3

Notes:
1. Actual attainable baud rate is limited by the latency of interrupt processing.
2. The middle of a start bit is detected as the 8th sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16th sample.
3. Guaranteed by design.

8 Ethernet: Three-Speed, MII Management

This section provides the AC and DC electrical characteristics for three-speed, 10/100/1000, and MII management.

8.1 Three-Speed Ethernet Controller (TSEC) (10/100/1000 Mbps)—GMII/MII/TBI/RGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to all GMII (gigabit media independent interface), the MII (media independent interface), TBI (ten-bit interface), RGMII (reduced gigabit media independent interface), and RTBI (reduced ten-bit interface) signals except MDIO (management data input/output) and MDC (management data clock). The RGMII and RTBI interfaces are defined for 2.5 V, while the GMII and TBI interfaces can be operated at 3.3 V or 2.5 V. Whether the GMII, MII, or TBI interface is operated at 3.3 or 2.5 V, the timing is compliant with the IEEE 802.3 standard. The RGMII and RTBI interfaces follow the Hewlett-Packard reduced pin-count interface for Gigabit Ethernet Physical Layer Device Specification Version 1.2a (9/22/2000). The electrical characteristics for MDIO and MDC are specified in Section 8.3, “Ethernet Management Interface Electrical Characteristics.”

8.1.1 TSEC DC Electrical Characteristics

All GMII, MII, TBI, RGMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 18 and Table 19. The potential applied to the input of a GMII, MII, TBI, RGMII, or RTBI receiver may exceed the potential of the receiver’s power supply (for example, a GMII driver powered from a 3.6-V supply driving V_{OH} into a GMII receiver powered from a 2.5-V supply). Tolerance for dissimilar GMII driver and receiver supply potentials is implicit in these specifications. The RGMII and RTBI signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 18. GMII, MII, and TBI DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	LV_{DD}	—		3.13	3.47	V
Output high voltage	V_{OH}	I_{OH} = –4.0 mA	LV_{DD} = Min	2.40	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 4.0 mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—	—	1.70	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	—	–0.3	0.90	V
Input high current	I_{IH}	V_{IN} [1] = LV_{DD}		—	40	µA
Input low current	I_{IL}	V_{IN} [1] = GND		–600	—	µA

Note:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

Table 19. GMII, MII, RGMII RTBI, and TBI DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit
Supply voltage 2.5 V	LV_{DD}	2.37	2.63	V
Output high voltage (LV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.00	LV_{DD} + 0.3	V
Output low voltage (LV_{DD} = Min, I_{OL} = 1.0 mA)	V_{OL}	GND – 0.3	0.40	V
Input high voltage (LV_{DD} = Min)	V_{IH}	1.70	LV_{DD} + 0.3	V
Input low voltage (LV_{DD} = Min)	V_{IL}	–0.3	0.70	V
Input high current (V_{IN} [1] = LV_{DD})	I_{IH}	—	10	µA
Input low current (V_{IN} [1] = GND)	I_{IL}	–15	—	µA

Note:
1. Note that the symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1and Table 2.

8.2.2.1 GMII Receive AC Timing Specifications

Table 21 provides the GMII receive AC timing specifications.

Table 21. GMII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock period	t_{GRX}	—	8.0	—	ns
RX_CLK duty cycle	t_{GRXH}/t_{GRX}	40	—	60	%
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{GRDVKH}	2.0	—	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{GRDXKH}	0.5	—	—	ns
RX_CLK clock rise and fall time	t_{GRXR}, t_{GRXF} [2,3]	—	—	1.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Signal timings are measured at 0.7 V and 1.9 V voltage levels.
3. Guaranteed by design.

Figure 8 provides the AC test load for TSEC.

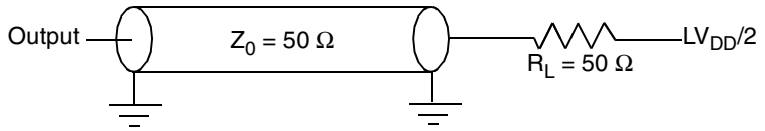

Figure 8. TSEC AC Test Load

Figure 9 shows the GMII receive AC timing diagram.

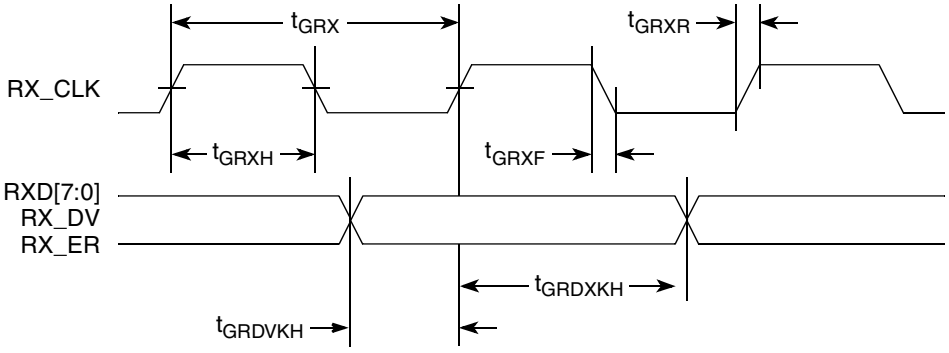

Figure 9. GMII Receive AC Timing Diagram

8.2.4.2 TBI Receive AC Timing Specifications

Table 25 provides the TBI receive AC timing specifications.

Table 25. TBI Receive AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock period	t_{TRX}		16.0		ns
RX_CLK skew	t_{SKTRX}	7.5	—	8.5	ns
RX_CLK duty cycle	t_{TRXH}/t_{TRX}	40	—	60	%
RCG[9:0] setup time to rising RX_CLK	t_{TRDVKH}	2.5	—	—	ns
RCG[9:0] hold time to rising RX_CLK	t_{TRDXKH}	1.5	—	—	ns
RX_CLK clock rise time and fall time	t_{TRXR}, t_{TRXF} [2,3]	0.7	—	2.4	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TRDVKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{TRX} clock reference (K) going to the high (H) state or setup time. Also, t_{TRDXKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the t_{TRX} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TRX} represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (TRX).
2. Guaranteed by design.

Figure 13 shows the TBI receive AC timing diagram.

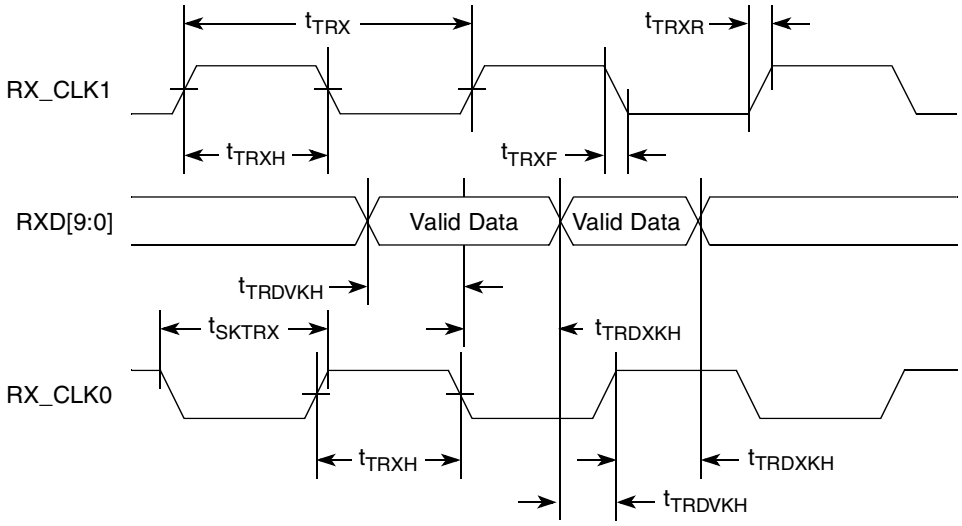

Figure 13. TBI Receive AC Timing Diagram

Figure 15 shows the MII management AC timing diagram.

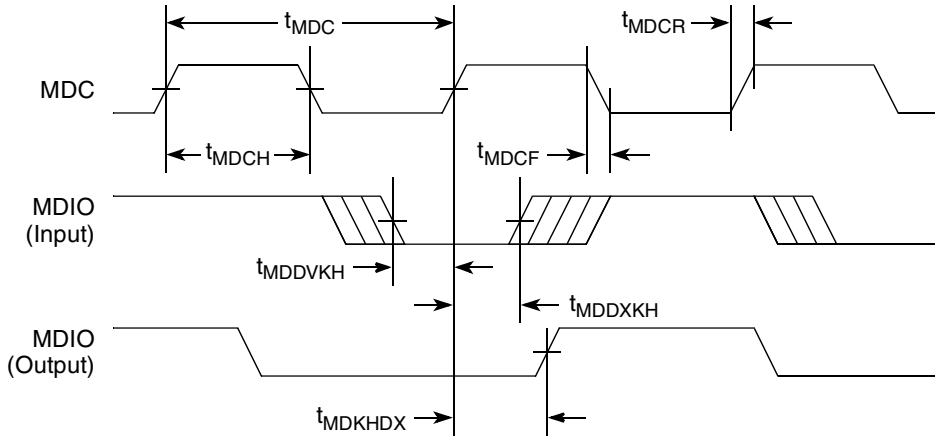

Figure 15. MII Management Interface Timing Diagram

9 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8555E.

9.1 Local Bus DC Electrical Characteristics

Table 29 provides the DC electrical characteristics for the local bus interface.

Table 29. Local Bus DC Electrical Characteristics

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V_{IH}	$V_{OUT} \geq V_{OH}$ (min) or	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	$V_{OUT} \leq V_{OL}$ (max)	–0.3	0.8	V
Input current	I_{IN}	V_{IN} [1] = 0 V or $V_{IN} = V_{DD}$	—	±5	μA
High-level output voltage	V_{OH}	OV_{DD} = min, I_{OH} = –2mA	OV_{DD} –0.2	—	V
Low-level output voltage	V_{OL}	OV_{DD} = min, I_{OL} = 2mA	—	0.2	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

Table 30. Local Bus General Timing Parameters—DLL Enabled (continued)

Parameter	Configuration [7]	Symbol [1]	Min	Max	Unit	Notes
Local bus clock to output high impedance for LAD/LDP	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKHOZ2}$	—	2.8	ns	5, 9
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			4.2		

Notes:
1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for DLL enabled mode.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of LSYNC_IN for DLL enabled to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. The value of t_{LBOTOT} is defined as the sum of 1/2 or 1 ccb_clk cycle as programmed by LBCR[AHD], and the number of local bus buffer delays used as programmed at power-on reset with configuration pins $\overline{\text{LWE}}[0:1]$.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $OV_{DD}/2$.
8. Guaranteed by characterization.
9. Guaranteed by design.

Table 31 describes the general timing parameters of the local bus interface of the MPC8555E with the DLL bypassed.

Table 31. Local Bus General Timing Parameters—DLL Bypassed

Parameter	Configuration [7]	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time		t_{LBK}	6.0	—	ns	2
Internal launch/capture clock to LCLK delay		t_{LBKHKT}	1.8	3.4	ns	8
LCLK[n] skew to LCLK[m] or LSYNC_OUT		$t_{LBKSKEW}$	—	150	ps	7, 9
Input setup to local bus clock (except LUPWAIT)		$t_{LBIVKH1}$	5.2	—	ns	3, 4
LUPWAIT input setup to local bus clock		$t_{LBIVKH2}$	5.1	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)		$t_{LBIXKH1}$	–1.3	—	ns	3, 4
LUPWAIT input hold from local bus clock		$t_{LBIXKH2}$	–0.8	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)		t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOV1}$	—	0.5	ns	3
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			2.0		
Local bus clock to data valid for LAD/LDP	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOV2}$	—	0.7	ns	3
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			2.2		

Figure 17 to Figure 22 show the local bus signals.

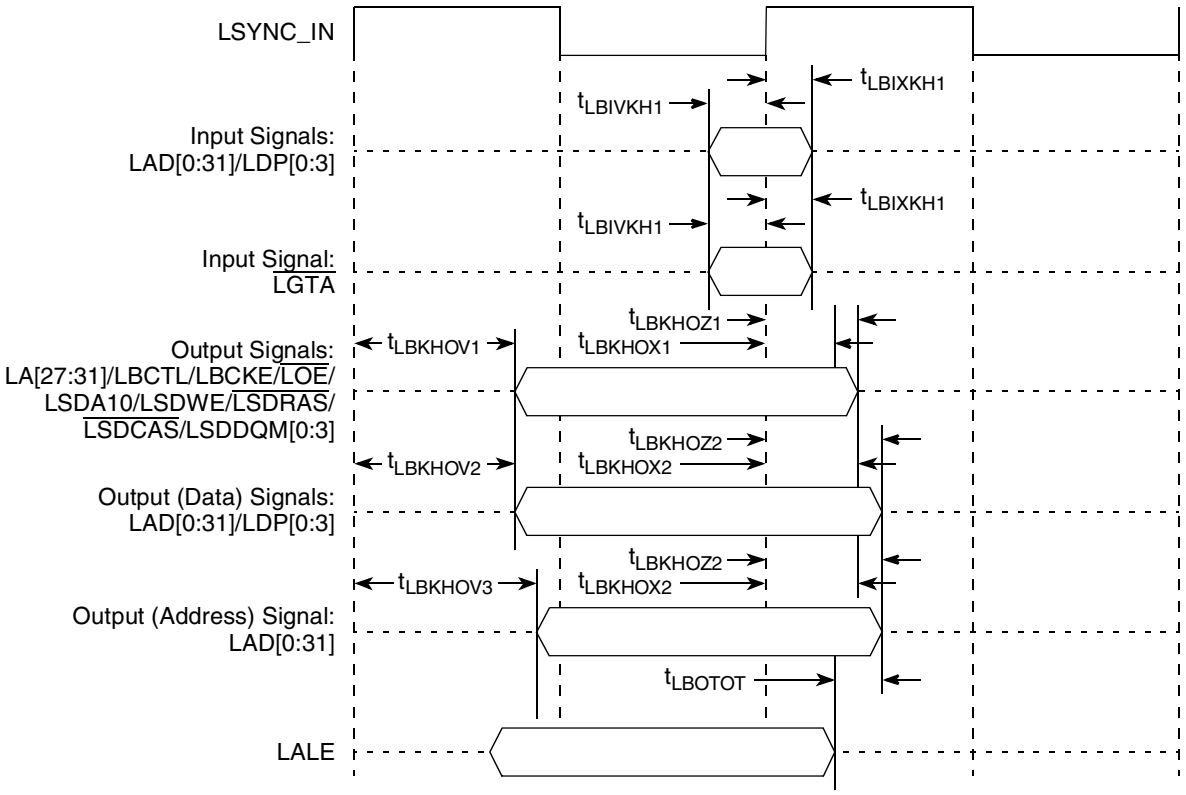

Figure 17. Local Bus Signals, Nonspecial Signals Only (DLL Enabled)

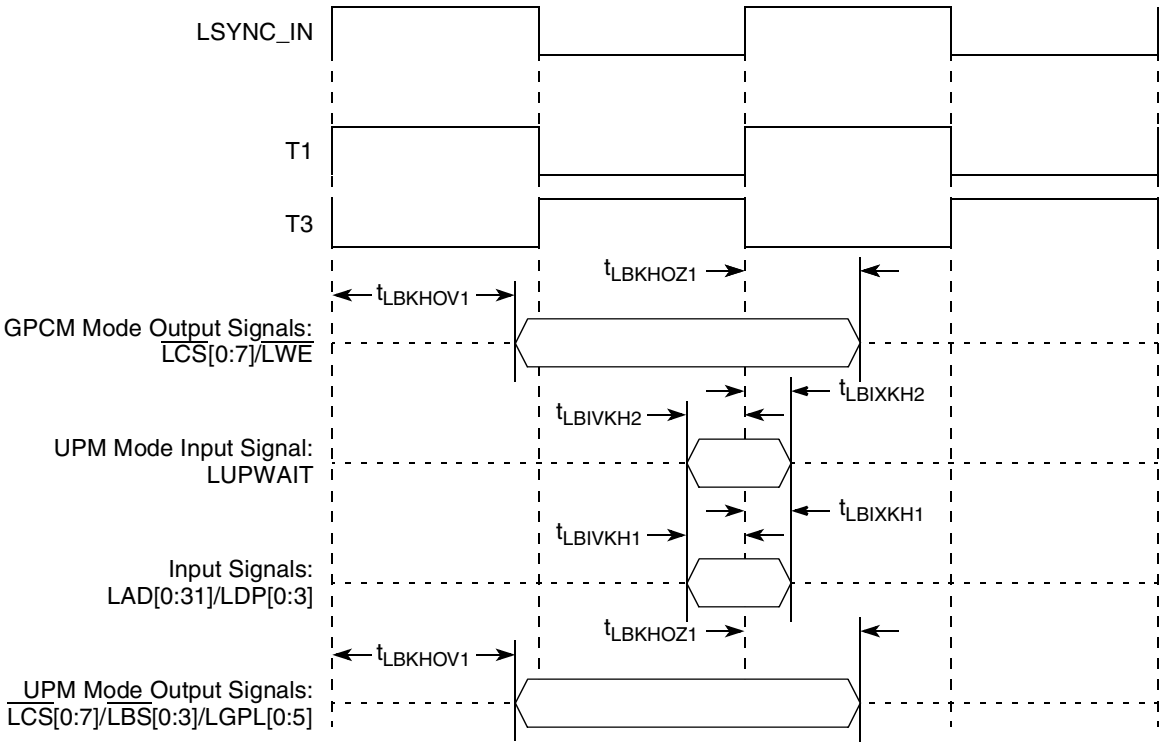

Figure 19. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Enabled)

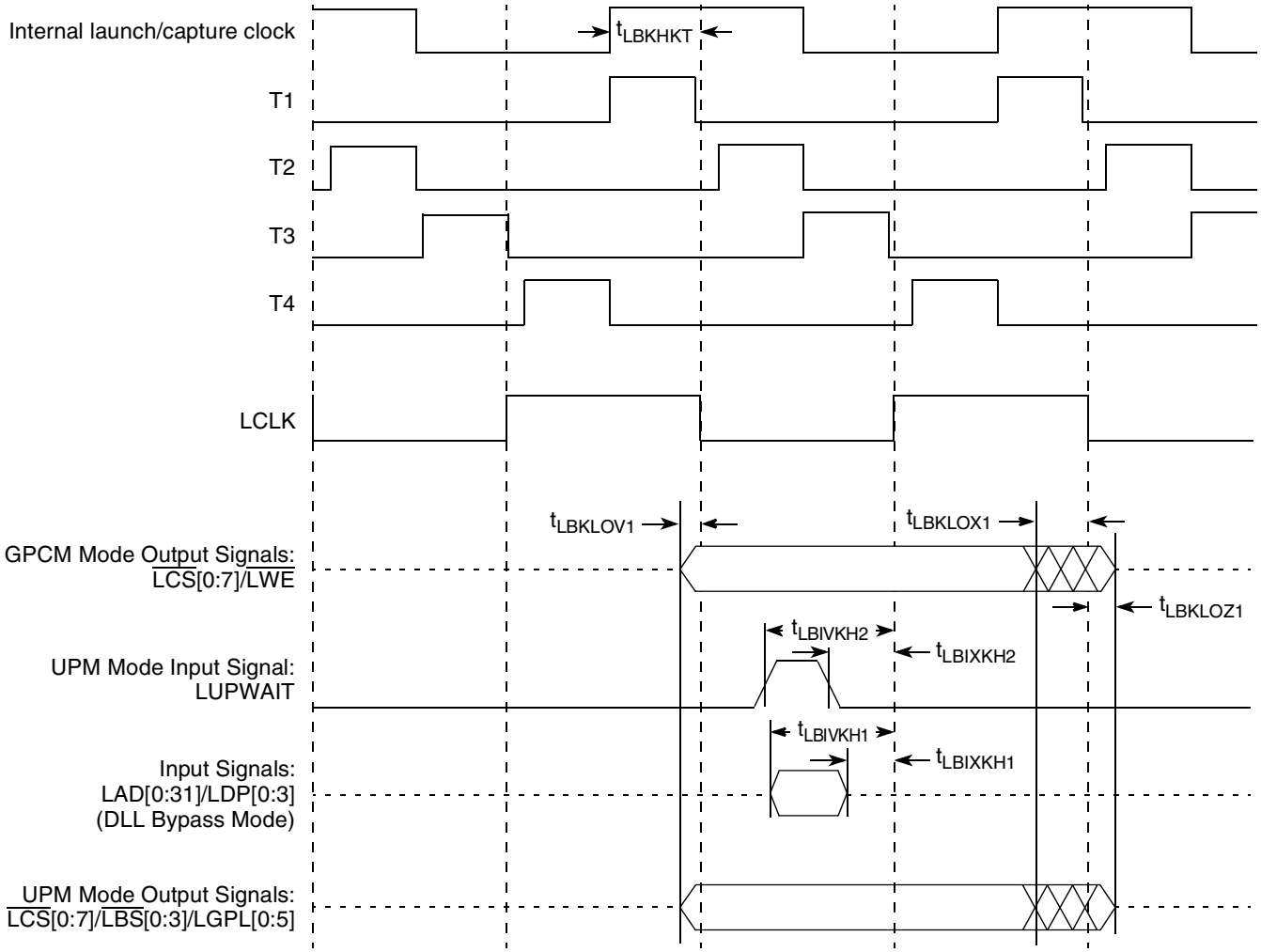

Figure 22. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 or 8 (DLL Bypass Mode)

10 CPM

This section describes the DC and AC electrical specifications for the CPM of the MPC8555E.

10.1 CPM DC Electrical Characteristics

Table 32 provides the DC electrical characteristics for the CPM.

Table 32. CPM DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Input high voltage	V_{IH}		2.0	3.465	V	1
Input low voltage	V_{IL}		GND	0.8	V	1, 2
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V	1
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V	1
Output high voltage	V_{OH}	I_{OH} = –2.0 mA	2.4	—	V	1
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V	1

Note:
1. This specification applies to the following pins: PA[0–31], PB[4–31], PC[0–31], and PD[4–31].
2. V_{IL}(max) for the IIC interface is 0.8 V rather than the 1.5 V specified in the IIC standard

10.2 CPM AC Timing Specifications

Table 33 and Table 34 provide the CPM input and output AC timing specifications, respectively.

NOTE: Rise/Fall Time on CPM Input Pins

It is recommended that the rise/fall time on CPM input pins should not exceed 5 ns. This should be enforced especially on clock signals. Rise time refers to signal transitions from 10% to 90% of VCC; fall time refers to transitions from 90% to 10% of VCC.

Table 33. CPM Input AC Timing Specifications [1]

Characteristic	Symbol [2]	Min[3]	Unit
FCC inputs—internal clock (NMSI) input setup time	t_{FIIVKH}	6	ns
FCC inputs—internal clock (NMSI) hold time	t_{FIIXKH}	0	ns
FCC inputs—external clock (NMSI) input setup time	t_{FEIVKH}	2.5	ns
FCC inputs—external clock (NMSI) hold time	t_{FEIXKH}b	2	ns
SCC/SMC/SPI inputs—internal clock (NMSI) input setup time	t_{NIIVKH}	6	ns
SCC/SMC/SPI inputs—internal clock (NMSI) input hold time	t_{NIIXKH}	0	ns
SCC/SMC/SPI inputs—external clock (NMSI) input setup time	t_{NEIVKH}	4	ns
SCC/SMC/SPI inputs—external clock (NMSI) input hold time	t_{NEIXKH}	2	ns
TDM inputs/SI—input setup time	t_{TDIVKH}	4	ns

Figure 32 provides the AC test load for TDO and the boundary-scan outputs of the MPC8555E.

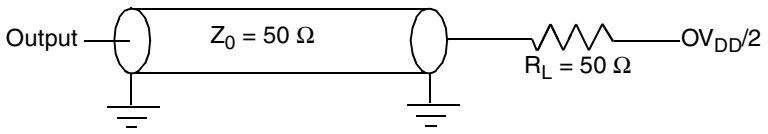

Figure 32. AC Test Load for the JTAG Interface

Figure 33 provides the JTAG clock input timing diagram.

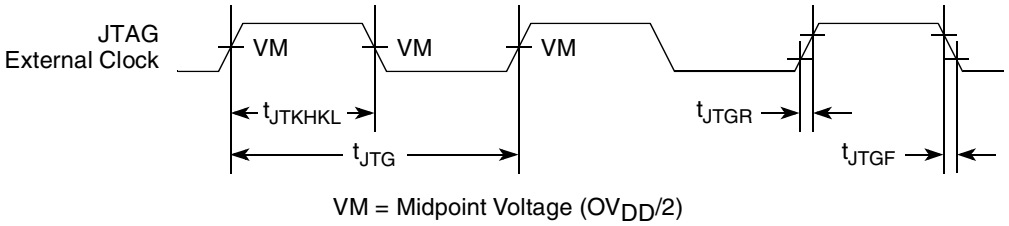

Figure 33. JTAG Clock Input Timing Diagram

Figure 34 provides the $\overline{\text{TRST}}$ timing diagram.

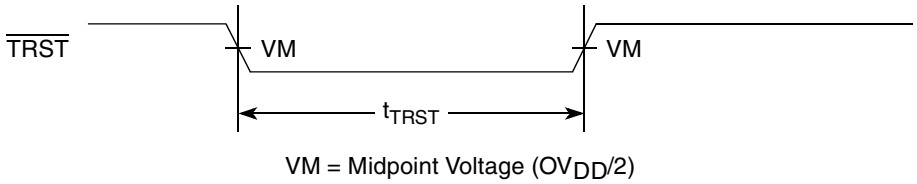

Figure 34. $\overline{\text{TRST}}$ Timing Diagram

Figure 35 provides the boundary-scan timing diagram.

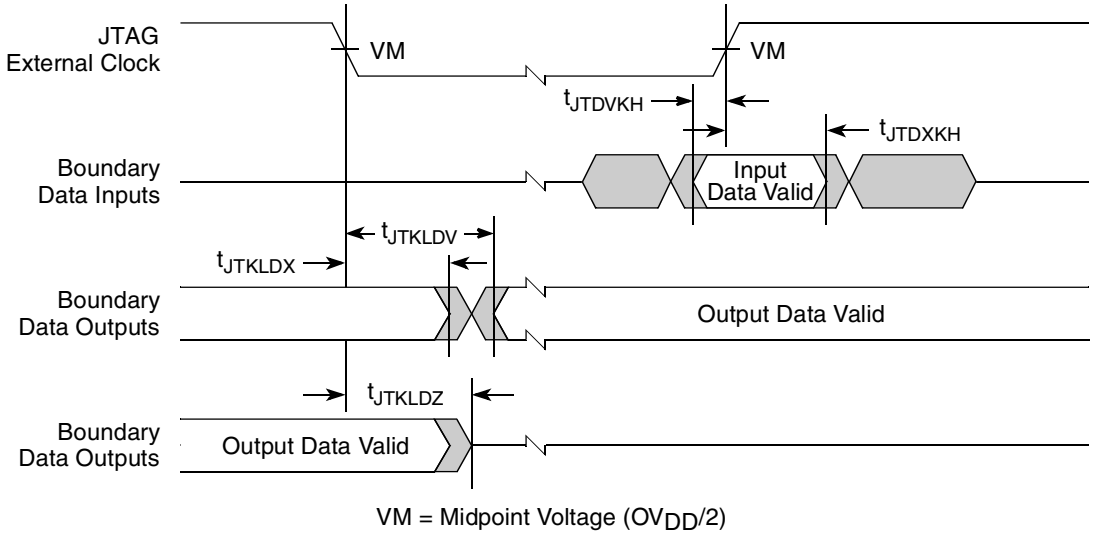

Figure 35. Boundary-Scan Timing Diagram

Ultimately, the final selection of an appropriate heat sink depends on many factors, such as thermal performance at a given air velocity, spatial volume, mass, attachment method, assembly, and cost. Several heat sinks offered by Aavid Thermalloy, Alpha Novatech, IERC, Chip Coolers, Millennium Electronics, and Wakefield Engineering offer different heat sink-to-ambient thermal resistances, that allows the MPC8555E to function in various environments.

16.2.1 Recommended Thermal Model

For system thermal modeling, the MPC8555E thermal model is shown in Figure 44. Five cuboids are used to represent this device. To simplify the model, the solder balls and substrate are modeled as a single block 29x29x1.6 mm with the conductivity adjusted accordingly. The die is modeled as 8.7 x 9.3 mm at a thickness of 0.75 mm. The bump/underfill layer is modeled as a collapsed resistance between the die and substrate assuming a conductivity of 4.4 W/m•K in the thickness dimension of 0.07 mm. The lid attach adhesive is also modeled as a collapsed resistance with dimensions of 8.7 x 9.3 x 0.05 mm and the conductivity of 1.07 W/m•K. The nickel plated copper lid is modeled as 11 x 11 x 1 mm.

Conductivity	Value	Unit
Lid ($11 \times 11 \times 1$ mm)		
k_x	360	W/(m × K)
k_y	360	
k_z	360	
Lid Adhesive—Collapsed resistance ($8.7 \times 9.3 \times 0.05$ mm)		
k_z	1.07	
Die ($8.7 \times 9.3 \times 0.75$ mm)		
Bump/Underfill—Collapsed resistance ($8.7 \times 9.3 \times 0.07$ mm)		
k_z	4.4	
Substrate and Solder Balls ($25 \times 25 \times 1.6$ mm)		
k_x	14.2	
k_y	14.2	
k_z	1.2	

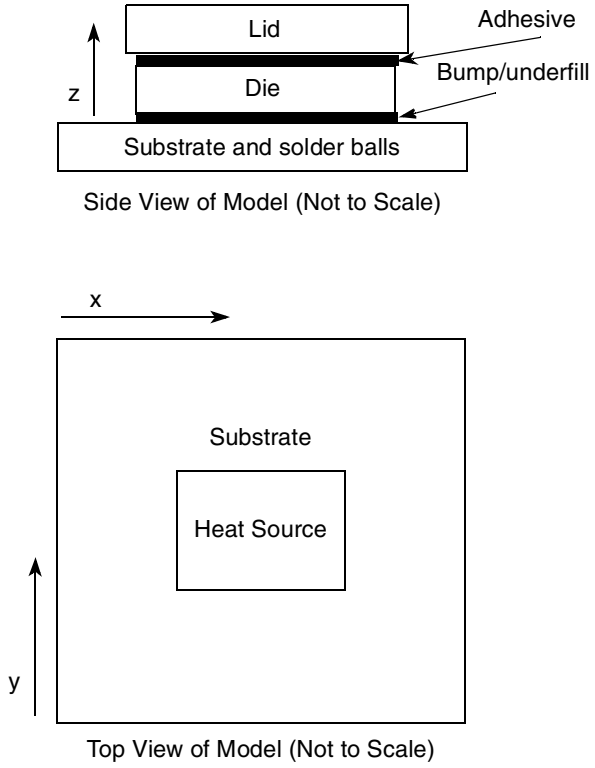

Figure 44. MPC8555E Thermal Model

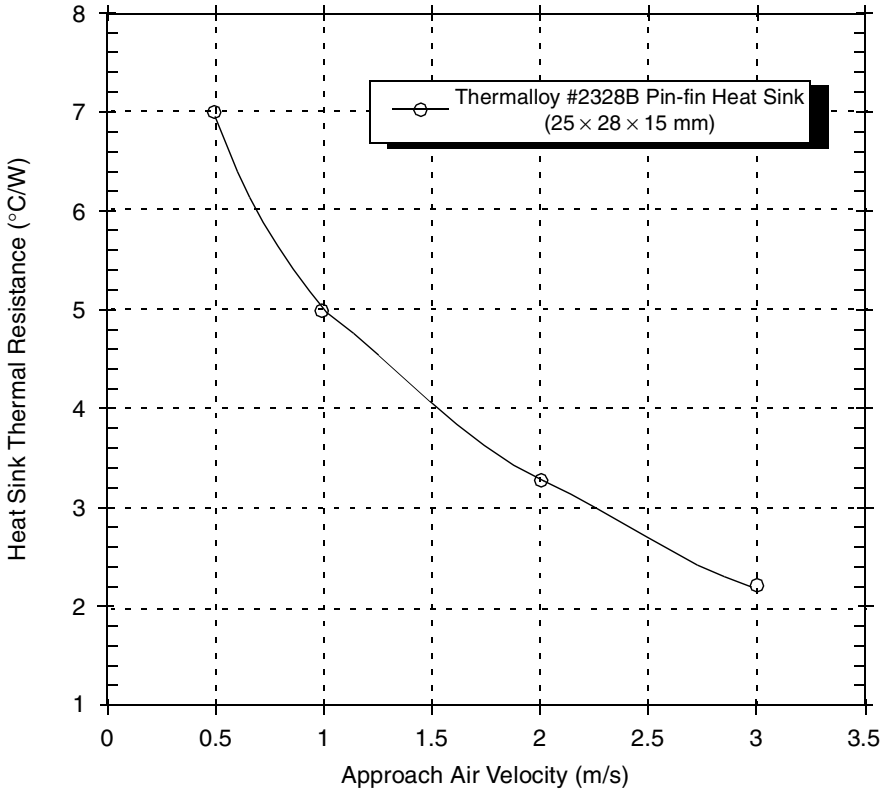

Figure 47. Thermalloy #2328B Heat Sink-to-Ambient Thermal Resistance Versus Airflow Velocity

16.2.4.2 Case 2

Every system application has different conditions that the thermal management solution must solve. As an alternate example, assume that the air reaching the component is 85 °C with an approach velocity of 1 m/sec. For a maximum junction temperature of 105 °C at 8 W, the total thermal resistance of junction to case thermal resistance plus thermal interface material plus heat sink thermal resistance must be less than 2.5 °C/W. The value of the junction to case thermal resistance in Table 49 includes the thermal interface resistance of a thin layer of thermal grease as documented in footnote 4 of the table. Assuming that the heat sink is flat enough to allow a thin layer of grease or phase change material, then the heat sink must be less than 1.5 °C/W.

Millennium Electronics (MEI) has tooled a heat sink MTHERM-1051 for this requirement assuming a compactPCI environment at 1 m/sec and a heat sink height of 12 mm. The MEI solution is illustrated in Figure 48 and Figure 49. This design has several significant advantages:

- The heat sink is clipped to a plastic frame attached to the application board with screws or plastic inserts at the corners away from the primary signal routing areas.
- The heat sink clip is designed to apply the force holding the heat sink in place directly above the die at a maximum force of less than 10 lbs.
- For applications with significant vibration requirements, silicone damping material can be applied between the heat sink and plastic frame.

When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

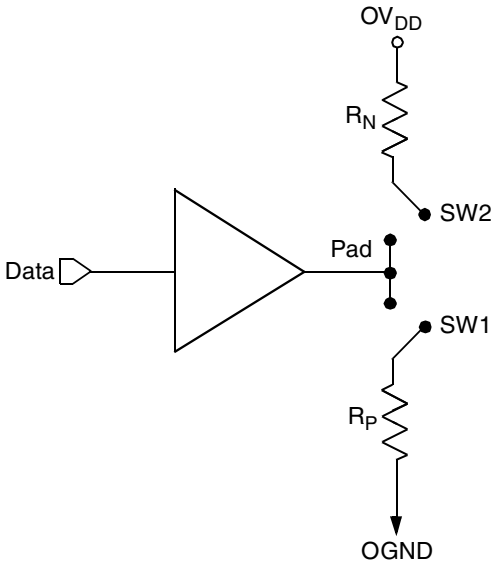

Figure 51. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term}. The measured voltage is $V_2 = 1/(1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1/V_2 - 1)$. The drive current is then $I_{source} = V_1/R_{source}$.

Table 50 summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD}, nominal OV_{DD}, 105°C.

Table 50. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
R_N	43 Target	25 Target	20 Target	Z_0	Ω
R_P	43 Target	25 Target	20 Target	Z_0	Ω
Differential	NA	NA	NA	Z_{DIFF}	Ω

Note: Nominal supply voltages. See Table 1, T_j = 105°C.